



First Named Inventor	Leonard Forbes	<b>GENERAL TRANSMITTAL FORM UNDER 37 CFR 1.8 (LARGE ENTITY)</b>
Serial No.	10/808,058	
Filing Date	March 24, 2004	
Group Art Unit	2818	
Examiner Name	Unknown	
Confirmation No.	4217	
Attorney Docket No.	400.288US01	
Title: MEMORY DEVICE WITH HIGH DIELECTRIC CONSTANT GATE DIELECTRICS AND METAL FLOATING GATES		

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<b>Enclosures</b>					
<b>The following documents are enclosed:</b>					
<input checked="" type="checkbox"/>	Information Disclosure Statement (1 pg.); Form 1449 (7 pgs.); 58 copies of cited references; U.S. reference(s) not included pursuant to 37 C.F.R. 1.98 (c)(2)(i);				
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<b>Submitted By</b>					
Name	Kenneth W. Bolvin	Reg. No.	34,125	Telephone	(612) 312-2211
Signature	<i>Kenneth W. Bolvin</i>			Date	9/2/04
<b>Certificate of Mailing</b>					
I certify that this correspondence and the identified documents listed on this transmittal are being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Mail Stop: AMENDMENT, Commissioner for Patents, P. O. Box 1450, Alexandria, VA 22313-1450 on September 2, 2004.					
Name	Rhonda L. Foley	Signature	<i>Rhonda L. Foley</i>		

(LARGE ENTITY TRANSMITTAL UNDER 37 CFR § 1.8)

First Named Inventor	Leonard Forbes	<b>INFORMATION DISCLOSURE STATEMENT</b>
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In compliance with 37 C.F.R. §§ 1.56 and 1.97, *et seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified Application. Pursuant to 37 C.F.R. 1.98 (a)(2)(i), as this application was filed after June 30, 2003, Applicant has not included copies of U.S. Patents or U.S. Patent Applications. Applicant respectfully requests that this Information Disclosure Statement be entered and the references listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to MPEP §609, Applicant further requests that the Examiner initial next to each reference on the Form 1449 to indicate that the listed references have been considered. Applicant further requests that a copy of the initialed Form 1449 be returned with the next official communication.

As an Office Action has not yet issued in this application, Applicant believes that no fees are due. However, the Commissioner for Patents is hereby authorized to charge any additional fees to Deposit Account No. 501373.

If the Examiner has any questions or concerns regarding this application, please contact the undersigned at (612) 312-2211.

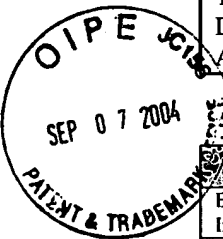
Respectfully submitted,

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	Certified Translation, "Flash cell that seeks to replace current technology introduced enabling both low cost and high performance" Nikkei Microdevices, November 1999, pp. 147-148.

Examiner Signature		Date Considered	
*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.			